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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

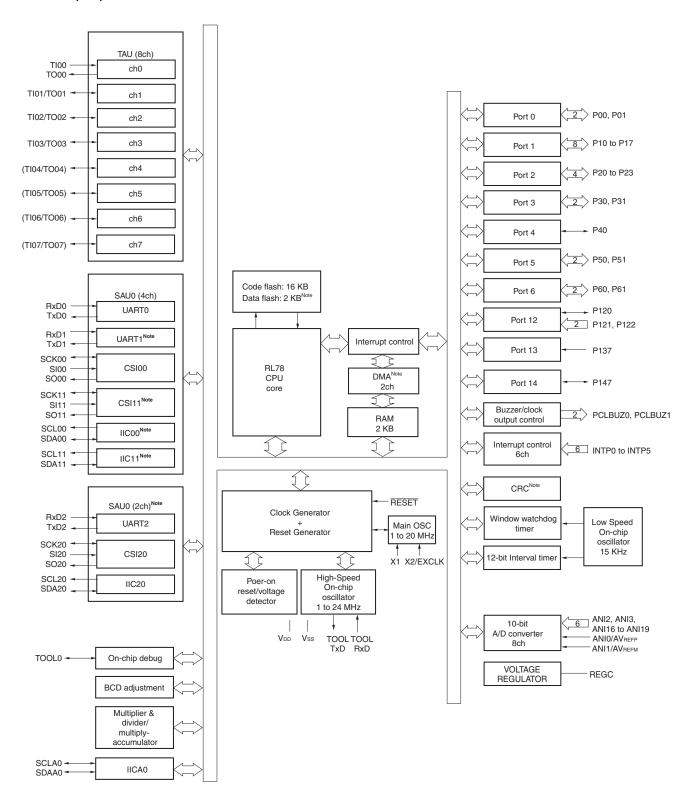
Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	14
Program Memory Size	12KB (12K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 11x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10269asp-x5

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

RL78/G12 1. OUTLINE

1.6.3 30-pin products



Note Provided only in the R5F102 products.

Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)**.

RL78/G12 1. OUTLINE

(2/2)

Item		20-	-pin	24-	-pin	30-	-pin			
		R5F1026x	R5F1036x	R5F1027x	R5F1037x	R5F102Ax	R5F103Ax			
Clock output/buzzer ou	ıtput			1		- 1	2			
		2.44 kHz to 10	MHz: (Peripher	al hardware cloc	ck: fmain = 20 MH	z operation)				
8/10-bit resolution A/D	converter		11 channels 8 channels							
Serial interface		[R5F1026x (20-pin), R5F1027x (24-pin)]								
		CSI: 2 chann	CSI: 2 channels/Simplified I ² C: 2 channels/UART: 1 channel							
		[R5F102Ax (30-pin)]								
		CSI: 1 chann	nel/Simplified I ² C	C: 1 channel/UAF	RT: 1 channel					
		CSI: 1 chann	nel/Simplified I ² C	C: 1 channel/UAF	RT: 1 channel					
		CSI: 1 chann	nel/Simplified I ² C	C: 1 channel/UAF	RT: 1 channel					
		[R5F1036x (20)-pin), R5F1037	x (24-pin)]						
		CSI: 1 chann	nel/Simplified I ² C	C: 0 channel/UAF	RT: 1 channel					
		[R5F103Ax (30	O-pin)]							
		CSI: 1 chann	nel/Simplified I ² C	C: 0 channel/UAF	RT: 1 channel					
	I ² C bus	1 channel								
Multiplier and divider/m	nultiply-	• 16 bits × 16 l	oits = 32 bits (ur	signed or signed	d)					
accumulator		• 32 bits × 32 l	oits = 32 bits (ur	isigned)						
		• 16 bits × 16 l	• 16 bits × 16 bits + 32 bits = 32 bits (unsigned or signed)							
DMA controller	1	2 channels	_	2 channels	_	2 channels	_			
Vectored interrupt	Internal	18	16	18	16	26	19			
sources	External			5		(6			
Key interrupt		(6	1	0	_				
Reset		 Internal rese Internal rese Internal rese Internal rese Internal rese 	Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access							
Power-on-reset circuit		Power-on-reset: 1.51 V (TYP) Power-down-reset: 1.50 V (TYP)								
Voltage detector		• Rising edge : 1.88 to 4.06 V (12 stages)								
		• Falling edge: 1.84 to 3.98 V (12 stages)								
On-chip debug function	n	Provided								
Power supply voltage		V _{DD} = 1.8 to 5.5 V								
Operating ambient tem	perature	$T_A = -40 \text{ to } +80$ (G: Industrial a	,	er applications,	D: Industrial app	olications), T _A = -	-40 to +105°C			

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

(2) 30-pin products

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit			
Supply	IDD2 Note 2	HALT	HS (High-speed	fin = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	1280	μА			
current Note 1		mode	main) mode Note 6		V _{DD} = 3.0 V		440	1280				
				fin = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	1000	μА			
					V _{DD} = 3.0 V		400	1000				
			LS (Low-speed	fin = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		260	530	μA			
			main) mode Note 6		V _{DD} = 2.0 V		260	530				
			HS (High-speed	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		280	1000	μА			
		main) mode Note 6	$V_{DD} = 5.0 \text{ V}$	Resonator connection		450	1170					
			$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		280	1000	μA				
			V _{DD} = 3.0 V	Resonator connection		450	1170					
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		190	600	μА			
				V _{DD} = 5.0 V	Resonator connection		260	670				
							$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		190	600	μΑ
				$V_{DD} = 3.0 \text{ V}$ $f_{MX} = 8 \text{ MHz}^{\text{Note 3}},$	Resonator connection		260	670				
			LS (Low-speed		Square wave input		95	330	μΑ			
			main) mode Note 6	V _{DD} = 3.0 V	Resonator connection		145	380				
				fmx = 8 MHz ^{Note 3}	Square wave input		95	330	μΑ			
				V _{DD} = 2.0 V	Resonator connection		145	380				
	IDD3 ^{Note 5}	STOP	$T_A = -40^{\circ}C$				0.18	0.50	μА			
		mode	T _A = +25°C				0.23	0.50				
			T _A = +50°C				0.30	1.10				
		-	T _A = +70°C				0.46	1.90				
			T _A = +85°C				0.75	3.30				

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator clock is stopped.
 - 4. When high-speed system clock is stopped.
 - 5. Not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: VDD = 2.7 V to 5.5 V @1 MHz to 24 MHz

 $V_{DD} = 2.4 \text{ V to } 5.5 \text{ V } @ 1 \text{ MHz to } 16 \text{ MHz}$

LS (Low speed main) mode: VDD = 1.8 V to 5.5 V @1 MHz to 8 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - 3. Except STOP mode, temperature condition of the TYP. value is $T_A = 25$ °C.

(3) Peripheral functions (Common to all products)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed onchip oscillator operating current	FIL Note 1				0.20		μΑ
12-bit interval timer operating current	ÎTMKA Notes 1, 2, 3				0.02		μΑ
Watchdog timer operating current	WDT Notes 1, 2, 4	fıL = 15 kHz			0.22		μΑ
A/D converter	IADC Notes 1, 5	When conversion at	Normal mode, AVREFP = VDD = 5.0 V		1.30	1.70	mA
operating current		maximum speed	Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.50	0.70	mA
A/D converter reference voltage operating current	ADREF Note 1				75.0		μΑ
Temperature sensor operating current	ITMPS Note 1				75.0		μА
LVD operating current	ILVD Notes 1, 6				0.08		μΑ
Self- programming operating current	FSP Notes 1, 8				2.00	12.20	mA
BGO operating current	IBGO Notes 1, 7				2.00	12.20	mA
SNOOZE	ISNOZ Note 1	ADC operation	The mode is performed Note 9		0.50	0.60	mA
operating current			The A/D conversion operations are performed, Low voltage mode, AVREFP = VDD = 3.0 V		1.20	1.44	mA
		CSI/UART operation			0.70	0.84	mA

Notes 1. Current flowing to the V_{DD} .

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IFIL and ITMKA when the 12-bit interval timer operates.
- 4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.
- **5.** Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **6.** Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit operates.
- 7. Current flowing only during data flash rewrite.
- 8. Current flowing only during self programming.
- 9. For shift time to the SNOOZE mode, see 17.3.3 SNOOZE mode.

Remarks 1. fil: Low-speed on-chip oscillator clock frequency

2. Temperature condition of the TYP. value is $T_A = 25^{\circ}C$

2.4 AC Characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Items	Symbol		Conditions				MAX.	Unit
Instruction cycle (minimum	Tcy	Main system	HS (High-	$2.7~V \leq V_{DD} \leq 5.5~V$	0.04167		1	μS
instruction execution time)		clock (fMAIN) operation	speed main) mode	$2.4~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$	0.0625		1	μS
			LS (Low- speed main) mode	$1.8~V \le V_{DD} \le 5.5~V$	0.125		1	μs
		During self	HS (High-	$2.7~V \leq V_{DD} \leq 5.5~V$	0.04167		1	μS
		programming	speed main) mode	$2.4~V \leq V_{DD} < 2.7~V$	0.0625		1	μS
			LS (Low- speed main) mode	$1.8~V \le V_{DD} \le 5.5~V$	0.125		1	μs
External main system clock	fex	$2.7~V \leq V_{DD} \leq 5$.5 V		1.0		20.0	MHz
frequency		$2.4~V \leq V_{DD} < 2$	1.0		16.0	MHz		
		$1.8~V \leq V_{DD} < 2$.4 V		1.0		8.0	MHz
External main system clock	texh, texl	$2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$						ns
input high-level width, low-level width		$2.4~V \leq V_{DD} < 2.7~V$			30			ns
level width		$1.8~V \leq V_{DD} < 2$.4 V	60			ns	
TI00 to TI07 input high-level width, low-level width	тпн, тп∟				1/fмск + 10			ns
TO00 to TO07 output	fто	4.0 V ≤ V _{DD} ≤ 5	.5 V				12	MHz
frequency		$2.7~V \leq V_{DD} < 4$.0 V				8	MHz
		1.8 V ≤ V _{DD} < 2	.7 V				4	MHz
PCLBUZ0, or PCLBUZ1	f PCL	4.0 V ≤ V _{DD} ≤ 5	.5 V				16	MHz
output frequency		$2.7~V \leq V_{DD} < 4$.0 V				8	MHz
		1.8 V ≤ V _{DD} < 2	.7 V				4	MHz
INTP0 to INTP5 input high- level width, low-level width	tinth, tintl				1			μS
KR0 to KR9 input available width	tĸĸ				250			ns
RESET low-level width	trsl				10			μS

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n bit of timer mode register 0 (TMR0n). n: Channel number (n = 0 to 7))

- Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.)
 - 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.))

(5) During communication at same potential (simplified I²C mode)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-speed	main) Mode	Unit
			LS (low-speed	main) Mode	
			MIN.	MAX.	
SCLr clock frequency	fscL	$1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V},$		400 Note 1	kHz
		$C_b=100~pF,~R_b=3~k\Omega$			
		$1.8 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V},$		300 Note 1	kHz
		$C_b=100~pF,~R_b=5~k\Omega$			
Hold time when SCLr = "L"	tLOW	$1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V},$	1150		ns
		$C_b=100~pF,~R_b=3~k\Omega$			
		$1.8 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V},$	1550		ns
		$C_b=100~pF,~R_b=5~k\Omega$			
Hold time when SCLr = "H"	tніgн	$1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$	1150		ns
		$C_b=100~pF,~R_b=3~k\Omega$			
		$1.8 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V},$	1550		ns
		$C_b=100~pF,~R_b=5~k\Omega$			
Data setup time (reception)	tsu:dat	$1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$	1/fмск + 145 Note 2		ns
		$C_b=100~pF,~R_b=3~k\Omega$			
		$1.8 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V},$	1/fмск + 230 Note 2		ns
		$C_b=100~pF,~R_b=5~k\Omega$			
Data hold time (transmission)	thd:dat	$1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V},$	0	355	ns
		$C_b=100~pF,~R_b=3~k\Omega$			
		$1.8 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V},$	0	405	ns
		$C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$			

- Notes 1. The value must also be equal to or less than fmck/4.
 - 2. Set tsu:DAT so that it will not exceed the hold time when SCLr = "L" or SCLr = "H".

Caution Select the N-ch open drain output (V_{DD} tolerance) mode for SDAr by using port output mode register h (POMh).

(Remarks are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	,	nigh-speed in) Mode		ow-speed n) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer rate Note4		Reception	$\begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_{b} \leq 4.0 \ V \end{aligned}$		fMCK/6 Note1		fMCK/6 Note1	bps
		Theoretical value of the maximum transfer rate $f_{\text{MCK}} = f_{\text{CLK}}$			4.0		1.3	Mbps
		$\begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V \end{split}$		fмск/6 Note1		fmck/6 Note1	bps	
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note3}$		4.0		1.3	Mbps
	$\begin{aligned} 1.8 \ V &\leq V_{\text{DD}} < 3.3 \ V, \\ 1.6 \ V &\leq V_{\text{b}} \leq 2.0 \ V \end{aligned}$		fMCK/6 Notes1, 2		fMCK/6 Notes1, 2	bps		
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note3}$		4.0		1.3	Mbps	
		Transmission	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		Note4		Note4	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.8 Note5		2.8 Note5	Mbps
			$\begin{aligned} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \end{aligned}$		Note6		Note6	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$		1.2 Note7		1.2 Note7	Mbps
			$1.8 \ V \le V_{DD} < 3.3 \ V,$ $1.6 \ V \le V_{b} \le 2.0 \ V$		Notes 2, 8		Notes 2, 8	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$		0.43 Note9		0.43 Note9	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2. Use it with $V_{DD} \ge V_b$.
- 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

16 MHz (2.4 V
$$\leq$$
 V_{DD} \leq 5.5 V)

LS (low-speed main) mode: $8 \text{ MHz} (1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V})$

4. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq V_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\left\{-C_b \times R_b \times \text{ln } (1-\frac{2.2}{V_b})\right\} \times 3} \quad \text{[bps]}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \text{ln} (1 - \frac{2.2}{\text{Vb}})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		h-speed Mode	LS (low-speed main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp [↑]) Note 1	tsıĸı	$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$	81		479		ns
		$ 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, $ $ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega $	177		479		ns
		$ \begin{aligned} 1.8 \ V &\leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ C_b &= 30 \ pF, \ R_b = 5.5 \ k\Omega \end{aligned} $			479		ns
SIp hold time (from SCKp↑) Note 1	tksi1	$ 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, $ $ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega $	19		19		ns
		$ 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, $ $ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega $	19		19		ns
		$\begin{split} 1.8 \ V & \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ C_b & = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	19		19		ns
Delay time from SCKp↓ to	tkso1	$ 4.0 \; V \leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, $ $ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega $		100		100	ns
SOp output Note 1		$2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V,$ $C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega$		195		195	ns
		$ \begin{aligned} 1.8 \ V &\leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ C_b &= 30 \ pF, \ R_b = 5.5 \ k\Omega \end{aligned} $		483		483	ns

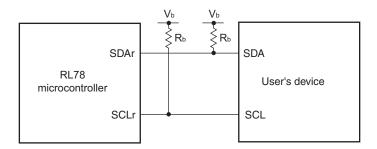
Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. Use it with $V_{DD} \ge V_b$.

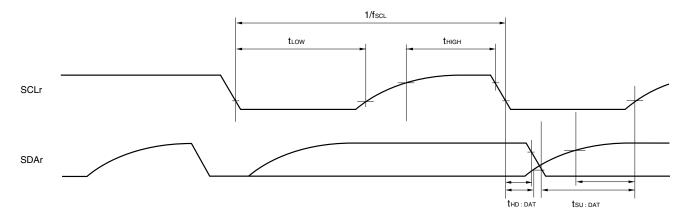
(Cautions and Remarks are listed on the next page.)



Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remarks 1.** Rb $[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, Cb [F]: Communication line (SDAr, SCLr) load capacitance, Vb [V]: Communication line voltage
 - **2.** r: IIC Number (r = 00, 20)
 - fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
 - m: Unit number (m = 0,1), n: Channel number (n = 0)
 - 4. Simplified I²C mode is supported only by the R5F102 products.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V}, \text{ Reference voltage (+)} = V_{DD}, \text{ Reference voltage (-)} = V_{SS})$

Parameter	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
Resolution	Res		8		10	bit	
Overall error ^{Note 1}	AINL	10-bit resolution			1.2	±7.0	LSB
					1.2	± 10.5 Note 3	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANIO to ANI3,	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
		ANI16 to ANI22	$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μs
				57		95	μS
Conversion time	tconv			2.375		39	μS
		Target pin: internal reference	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	3.5625		39	μS
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution				±0.60	%FSR
						±0.85	%FSR
Full-scale errorNotes 1, 2	EFS	10-bit resolution				±0.60	%FSR
						±0.85	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution				±4.0	LSB
						±6.5 Note 3	LSB
Differential linearity error Note 1	DLE	10-bit resolution				±2.0	LSB
						±2.5 Note 3	LSB
Analog input voltage	VAIN	ANI0 to ANI3, ANI16 to ANI2	2	0		V _{DD}	V
	Internal reference voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)			V _{BGR} Note 4			V
		Temperature sensor output v (2.4 V \leq VDD \leq 5.5 V, HS (high	•		VTMPS25 Note 4	1	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).
- 4. Refer to 28.6.2 Temperature sensor/internal reference voltage characteristics.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(3/4)

Parameter	Symbol	Condition	S	MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	Normal input buffer	<u>- </u>	0.8V _{DD}		V _{DD}	V
		20-, 24-pin products: P00 to P0 P40 to P42	03 ^{Note 2} , P10 to P14,				
		30-pin products: P00, P01, P1 P40, P50, P51, P120, P147					
	V _{IH2}	TTL input buffer	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	2.2		V _{DD}	٧
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	2.0		V _{DD}	٧
		30-pin products: P01, P10, P11, P13 to P17	2.4 V ≤ V _{DD} < 3.3 V	1.5		V _{DD}	V
	V _{IH3}	Normal input buffer P20 to P23	0.7V _{DD}		V _{DD}	V	
	V _{IH4}	P60, P61	0.7V _{DD}		6.0	V	
	V _{IH5}	P121, P122, P125 ^{Note 1} , P137, I	0.8V _{DD}		V _{DD}	V	
Input voltage, low	V _{IL1}	Normal input buffer	0		0.2V _{DD}	V	
		20-, 24-pin products: P00 to P0 P40 to P42	03 ^{Note 2} , P10 to P14,				
		30-pin products: P00, P01, P10 P40, P50, P51, P120, P147					
	V _{IL2}	TTL input buffer	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	0		0.8	٧
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	0		0.5	٧
		30-pin products: P01, P10, P11, P13 to P17		0		0.32	V
	V _{IL3}	P20 to P23		0		0.3V _{DD}	٧
	V _{IL4}	P60, P61		0		0.3V _{DD}	٧
	V _{IL5}	P121, P122, P125 ^{Note 1} , P137, I	EXCLK, RESET	0		0.2V _{DD}	V
Output voltage, high	V _{OH1}	20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14,	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	V _{DD} -0.7			V
		P40 to P42 30-pin products:	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -2.0 \text{ mA}$	V _{DD} -0.6			V
		P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -1.5 \text{ mA}$	V _{DD} -0.5			V
	V _{OH2}	P20 to P23	Іон2 = -100 μΑ	V _{DD} -0.5			V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode. High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le VDD \le 5.5 \text{ V}, Vss = 0 \text{ V})$

(4/4)

Parameter	Symbol		Conditio	ns	MIN.	TYP.	MAX.	Unit
Output voltage, low	V _{OL1}		20-, 24-pin products: 4 P00 to P03 ^{Note} , P10 to P14, lc				0.7	V
		30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147 $\begin{vmatrix} 1 & 1 & 1 & 1 & 1 & 1 & 1 & 1 & 1 & 1 $		$2.7~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 3.0~mA$			0.6	V
				$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V},$ $\text{IoL1} = 1.5 \text{ mA}$			0.4	V
				$2.4~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 0.6~mA$			0.4	٧
	V _{OL2}	P20 to P23		Ιοι2 = 400 μΑ			0.4	V
	Vol3	P60, P61		$4.0~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 15.0~mA$			2.0	V
		2		$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 5.0 \text{ mA}$			0.4	V
				$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $I_{\text{OL1}} = 3.0 \text{ mA}$			0.4	V
				$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 2.0 \text{ mA}$			0.4	V
Input leakage current, high	Ішн1	Other than P121, V _I = V _{DD} P122					1	μА
	ILIH2	P121, P122 (X1, X2/EXCLK)	VI = VDD	Input port or external clock input			1	μА
				When resonator connected			10	μΑ
Input leakage current, low	ILIL1	Other than P121, P122	Vı = Vss				-1	μΑ
	ILIL2	P121, P122 (X1, X2/EXCLK)	Vı = Vss	Input port or external clock input			-1	μΑ
				When resonator connected			-10	μΑ
On-chip pull-up resistance	Rυ	20-, 24-pin product P00 to P03 ^{Note} , P10 P40 to P42, P125,) to P14,	V _I = V _{SS} , input port	10	20	100	kΩ
		30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147						

Note 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

(1) 20-, 24-pin products

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

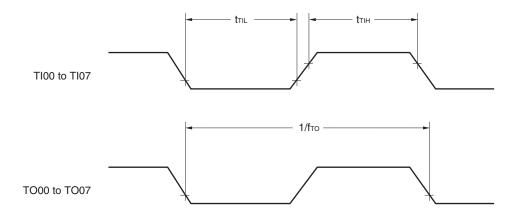
Parameter	Symbol		Conditions						MAX.	Unit					
Supply	I _{DD1}	Operating	HS (High-speed	f⊪ = 24 MHz ^{Note 3}	Basic	V _{DD} = 5.0 V		1.5		mA					
current ^{Note 1}		mode	main) mode Note 4		operation	V _{DD} = 3.0 V		1.5							
					Normal	V _{DD} = 5.0 V		3.3	5.3	mA					
					operation	V _{DD} = 3.0 V		3.3	5.3						
				f⊪ = 16 MHz ^{Note 3}		V _{DD} = 5.0 V		2.5	3.9	mA					
						V _{DD} = 3.0 V		2.5	3.9						
			$f_{MX} = 20 \text{ MHz}^{\text{Note 2}}$ $V_{DD} = 5.0 \text{ V}$		Square wave input		2.8	4.7	mA						
				$V_{DD} = 5.0 \text{ V}$		Resonator connection		3.0	4.8						
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$		Square wave input		2.8	4.7	mA					
	V _{DD} = 3.0 V					$V_{DD} = 3.0 \text{ V}$	$V_{DD} = 3.0 \text{ V}$	$V_{DD} = 3.0 \text{ V}$	V _{DD} = 3.0 V		Resonator connection		3.0	4.8	
				fmx = 10 MHz ^{Note 2} ,		Square wave input		1.8	2.8	mA					
				$V_{DD} = 5.0 \text{ V}$		Resonator connection		1.8	2.8						
				fmx = 10 MHz ^{Note 2} ,		Square wave input		1.8	2.8	mA					
				$V_{DD} = 3.0 \text{ V}$		Resonator connection		1.8	2.8						

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator clock is stopped.
 - 3. When high-speed system clock is stopped
 - **4.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

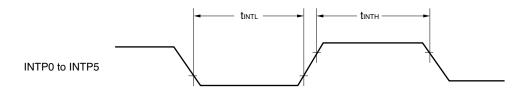
HS(High speed main) mode: $V_{DD} = 2.7 \text{ V to } 5.5 \text{ V } @ 1 \text{ MHz to } 24 \text{ MHz}$ $V_{DD} = 2.4 \text{ V to } 5.5 \text{ V } @ 1 \text{ MHz to } 16 \text{ MHz}$

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - **3.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$.

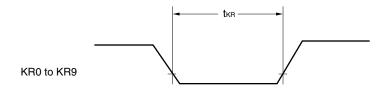
TI/TO Timing



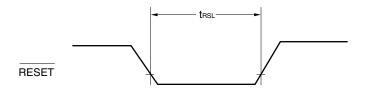
Interrupt Request Input Timing



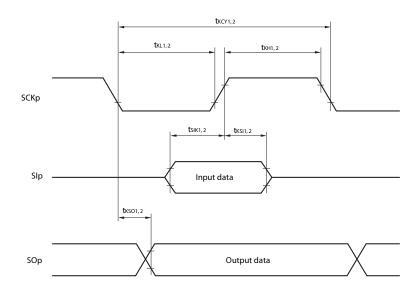
Key Interrupt Input Timing



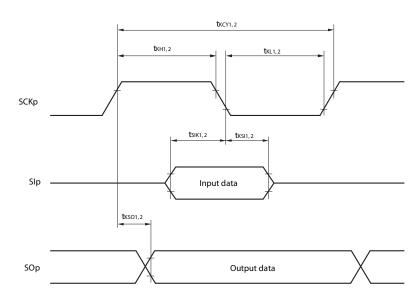
RESET Input Timing



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0,1), n: Channel number (n = 0, 1, 3))

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.
- 5. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq V_{DD} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln{(1-\frac{2.0}{V_b})}\} \times 3} \text{ [bps]}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.
- 7. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq VDD < 3.3 V, 1.6 V \leq Vb \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **8.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 7** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.



3.5.2 Serial interface IICA

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions HS (high-speed main) mode			node	Unit	
			Standa	rd Mode	Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fclk≥ 3.5 MHz			0	400	kHz
		Normal mode: fclk≥ 1 MHz	0	100			kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μS
Hold time ^{Note 1}	thd:sta		4.0		0.6		μS
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μS
Hold time when SCLA0 = "H"	thigh		4.0		0.6		μS
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission) ^{Note 2}	thd:dat		0	3.45	0	0.9	μS
Setup time of stop condition	tsu:sto		4.0		0.6		μS
Bus-free time	t BUF		4.7		1.3		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

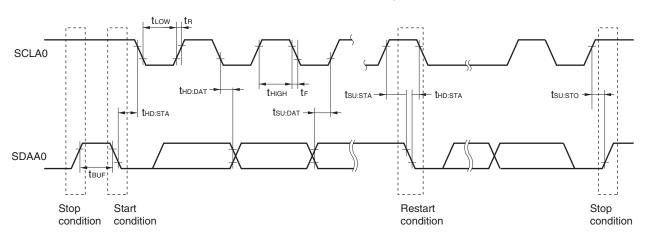
2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VoH1, VoL1) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Normal mode: $C_b = 400 \text{ pF}, \text{ Rb} = 2.7 \text{ k}\Omega$ Fast mode: $C_b = 320 \text{ pF}, \text{ Rb} = 1.1 \text{ k}\Omega$

IICA serial transfer timing



<R>



3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage				
	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = VDD Reference voltage (-) = Vss	Reference voltage (+) = VBGR Reference voltage (-) = AVREFM		
ANI0 to ANI3	Refer to 29.6.1 (1) .	Refer to 29.6.1 (3).	Refer to 29.6.1 (4).		
ANI16 to ANI22	Refer to 29.6.1 (2).				
Internal reference voltage	Refer to 29.6.1 (1) .		=		
Temperature sensor output voltage					

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cor	MIN.	TYP.	MAX.	Unit	
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AVREFP = VDD Note 3			1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution Target pin: ANI2, ANI3	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	EZS	10-bit resolution AVREFP = VDD Note 3				±0.25	%FSR
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution AVREFP = VDD Note 3			±0.25	%FSR	
Integral linearity error ^{Note 1}	ILE	10-bit resolution AVREFP = VDD Note 3			±2.5	LSB	
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} Note 3				±1.5	LSB
Analog input voltage	Vain	ANI2, ANI3		0		AVREFP	V
		Internal reference voltage (HS (high-speed main) m			V _{BGR} Note 4		V
		Temperature sensor outp	· ·	V _{TMPS25} Note 4		V	

(Notes are listed on the next page.)



3.9 Dedicated Flash Memory Programmer Communication (UART)

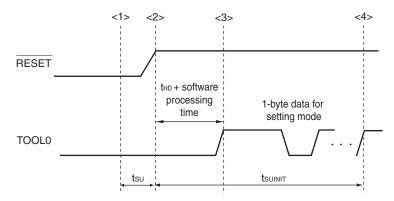
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

1 11 1, = = 1 1,						
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset are released before external release			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset are released before external release	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released	thd	POR and LVD reset are released before external release	1			ms
(excluding the processing time of the firmware to control the flash memory)						



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)



		Description			
Rev.	Date	Page	Summary		
2.00	Sep 06, 2013	55	Modification of description and Notes 3 and 4 in 2.6.1 (3)		
		56	Modification of description and Notes 3 and 4 in 2.6.1 (4)		
		57	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics		
		57	Modification of table and Note in 2.6.3 POR circuit characteristics		
		58	Modification of table in 2.6.4 LVD circuit characteristics		
		59	Modification of table of LVD detection voltage of interrupt & reset mode		
		59	Modification of number and title to 2.6.5 Power supply voltage rising slope characteristics		
		61	Modification of table, figure, and Remark in 2.10 Timing of Entry to Flash Memory		
			Programming Modes		
		62 to 103	Addition of products of industrial applications (G: Ta = -40 to +105°C)		
		104 to 106	Addition of products of industrial applications (G: $TA = -40 \text{ to } +105^{\circ}\text{C}$)		
2.10	Mar 25, 2016	6	Modification of Figure 1-1 Part Number, Memory Size, and Package of RL78/G12		
		7	Modification of Table 1-1 List of Ordering Part Numbers		
		8	Addition of product name (RL78/G12) and description (Top View) in 1.4.1 20-pin products		
		9	Addition of product name (RL78/G12) and description (Top View) in 1.4.2 24-pin products		
		10	Addition of product name (RL78/G12) and description (Top View) in 1.4.3 30-pin products		
		15	Modification of description in 1.7 Outline of Functions		
		16	Modification of description, and addition of target products		
		52	Modification of note 2 in 2.5.2 Serial interface IICA		
		60	Modification of title and note, and addition of caution in 2.7 RAM Data Retention Characteristics		
		60	Modification of conditions in 2.8 Flash Memory Programming Characteristics		
		62	Modification of description, and addition of target products and remark		
		94	Modification of note 2 in 3.5.2 Serial interface IICA		
		102	Modification of title and note in 3.7 RAM Data Retention Characteristics		
		102	Modification of conditions in 3.8 Flash Memory Programming Characteristics		
		104 to 106	Addition of package name		

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